

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CBR6M-L010 SERIES

SILICON BRIDGE RECTIFIER
6.0 AMP, 100 THRU 1000 VOLTS

CASE DM

DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR6M-L010 series types are silicon single phase full wave bridge rectifiers designed for general purpose, high current applications.

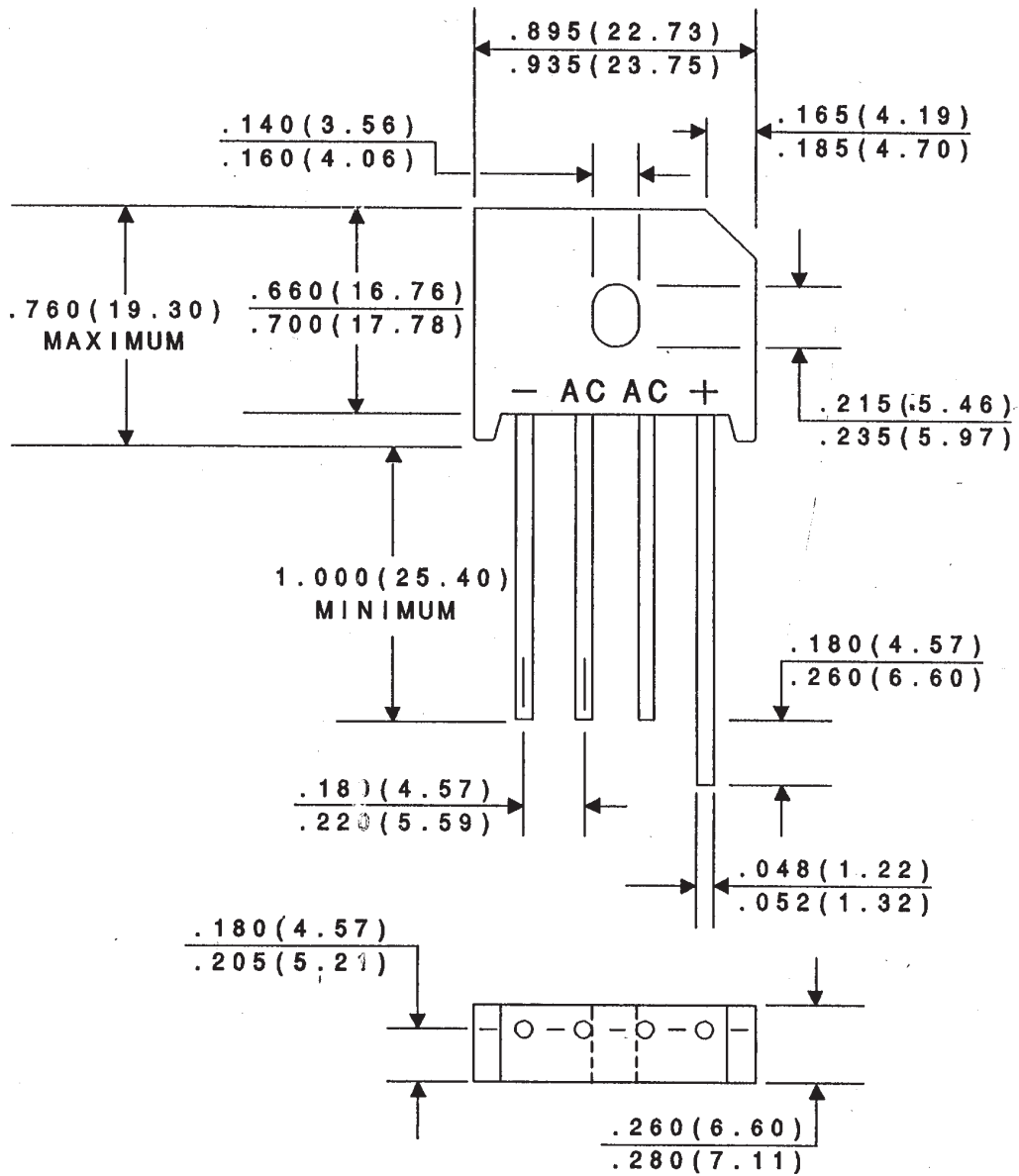
MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

	<u>SYMBOL</u>	<u>CBR6M</u> <u>-L010</u>	<u>CBR6M</u> <u>-L020</u>	<u>CBR6M</u> <u>-L040</u>	<u>CBR6M</u> <u>-L060</u>	<u>CBR6M</u> <u>-L080</u>	<u>CBR6M</u> <u>-L100</u>	<u>UNITS</u>
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current ($T_C = 100^\circ\text{C}$)	I_O			6.0				A
Peak Forward Surge Current	I_{FSM}			250				A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +150				$^\circ\text{C}$
Thermal Resistance	θ_{JC}			3.5				$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
V_F	$I_F = 6.0\text{A}$		1.1	V
I_R	$V_R = \text{Rated } V_{RRM}$		10	μA
I_R	$V_R = \text{Rated } V_{RRM}, T_C = 100^\circ\text{C}$		200	μA

CASE DM - MECHANICAL OUTLINE



All Dimensions in inches (mm).

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